

**Description**

The SX2305BI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = -20V$   $I_D = -6.2A$

$R_{DS(ON)} < 36m\Omega$  @  $V_{GS} = -4.5V$

**Application**

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings ( $T_c=25^\circ C$  unless otherwise noted)**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-6.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-5.1	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-36	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>3</sup>	4.31	W
$P_D @ T_A = 70^\circ C$	Total Power Dissipation <sup>3</sup>	0.84	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	125	$^\circ C/W$
$R_{\theta JC}$	Thermal resistance, junction-case	7.4	$^\circ C/W$

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_D=-250\mu\text{A}$	-20	-23	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	$\text{BV}_{\text{DSS}}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$	---	-0.014	---	$\text{V}/^\circ\text{C}$
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{\text{GS}}=-4.5\text{V}$ , $I_D=-4.9\text{A}$	---	30	36	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}$ , $I_D=-3.4\text{A}$	---	36	45	
		$V_{\text{GS}}=-1.8\text{V}$ , $I_D=-2\text{A}$	---	50	70	
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D=-250\mu\text{A}$	-0.5	-0.65	-1.2	V
$\Delta V_{\text{GS}(\text{th})}$	$V_{\text{GS}(\text{th})}$ Temperature Coefficient		---	3.95	---	$\text{mV}/^\circ\text{C}$
$I_{\text{DSS}}$	Drain-Source Leakage Current	$V_{\text{DS}}=-16\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	-1	$\text{uA}$
		$V_{\text{DS}}=-16\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=55^\circ\text{C}$	---	---	-5	
$I_{\text{GSS}}$	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 12\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA
$g_{\text{fs}}$	Forward Transconductance	$V_{\text{DS}}=-5\text{V}$ , $I_D=-3\text{A}$	---	12.8	---	S
$Q_g$	Total Gate Charge (-4.5V)	$V_{\text{DS}}=-15\text{V}$ , $V_{\text{GS}}=-4.5\text{V}$ , $I_D=-3\text{A}$	---	10.2	14.3	nC
$Q_{\text{gs}}$	Gate-Source Charge		---	1.89	2.6	
$Q_{\text{gd}}$	Gate-Drain Charge		---	3.1	4.3	
$T_{\text{d}(\text{on})}$	Turn-On Delay Time	$V_{\text{DD}}=-10\text{V}$ , $V_{\text{GS}}=-4.5\text{V}$ , $R_G=3.3\Omega$ , $I_D=-3\text{A}$	---	5.6	11.2	ns
$T_r$	Rise Time		---	40.8	73	
$T_{\text{d}(\text{off})}$	Turn-Off Delay Time		---	33.6	67	
$T_f$	Fall Time		---	18	36	
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=-15\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	857	1200	pF
$C_{\text{oss}}$	Output Capacitance		---	114	160	
$C_{\text{rss}}$	Reverse Transfer Capacitance		---	108	151	
$I_s$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0\text{V}$ , Force Current	---	---	-4.9	A
$I_{\text{SM}}$	Pulsed Source Current <sup>2,4</sup>		---	---	-14	A
$V_{\text{SD}}$	Diode Forward Voltage <sup>2</sup>	$V_{\text{GS}}=0\text{V}$ , $I_s=-1\text{A}$ , $T_J=25^\circ\text{C}$	---	---	-1	V
$t_{\text{rr}}$	Reverse Recovery Time	IF=-3A, $\text{di}/\text{dt}=100\text{A}/\mu\text{s}$ , $T_J=25^\circ\text{C}$	---	21.8	---	nS
$Q_{\text{rr}}$	Reverse Recovery Charge		---	6.9	---	nC

Note :

- 1、The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\Delta 300\mu\text{s}$  , duty cycle  $\Delta 2\%$
- 3、The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4、The data is theoretically the same as  $I_D$  and  $I_{\text{DM}}$  , in real applications , should be limited by total power dissipation.

## Typical Characteristics

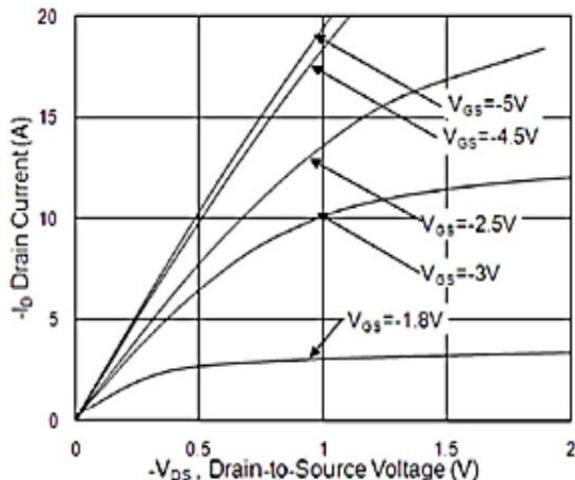


Fig.1 Typical Output Characteristics

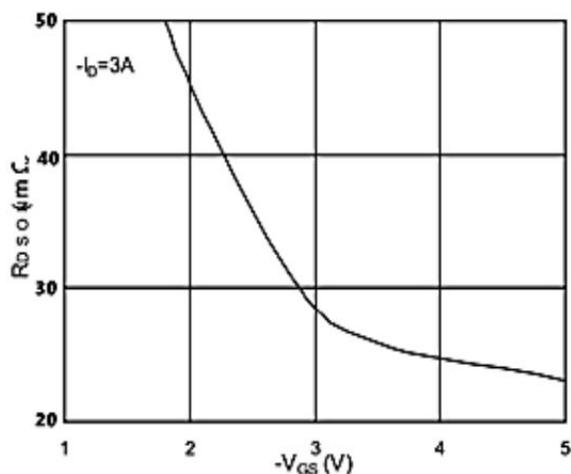


Fig.2 On-Resistance vs. G-S Voltage

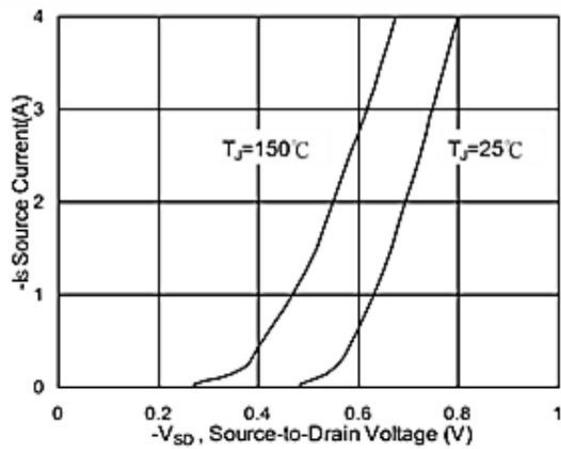


Fig.3 Forward Characteristics of Reverse

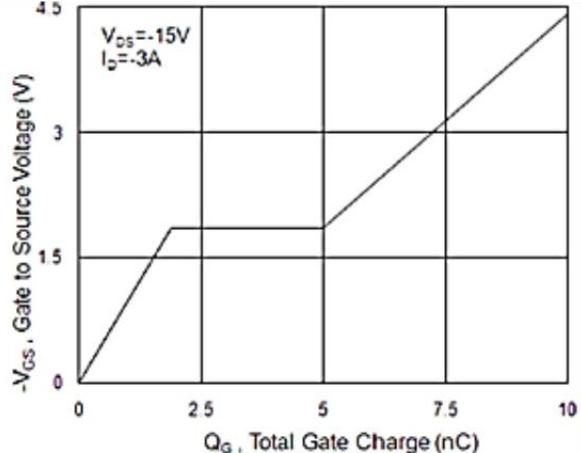
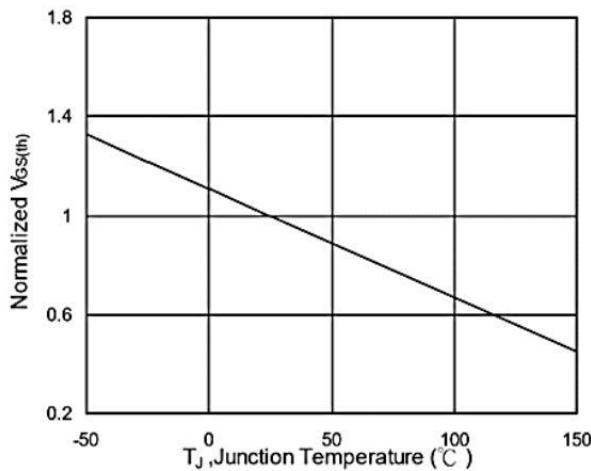
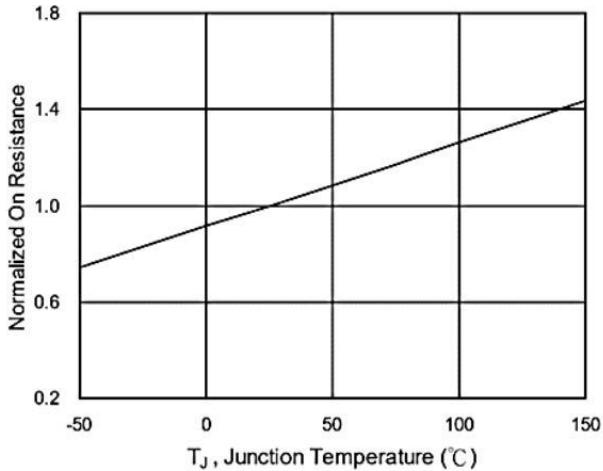


Fig.4 Gate-charge Characteristics

Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$ Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

## Typical Characteristics

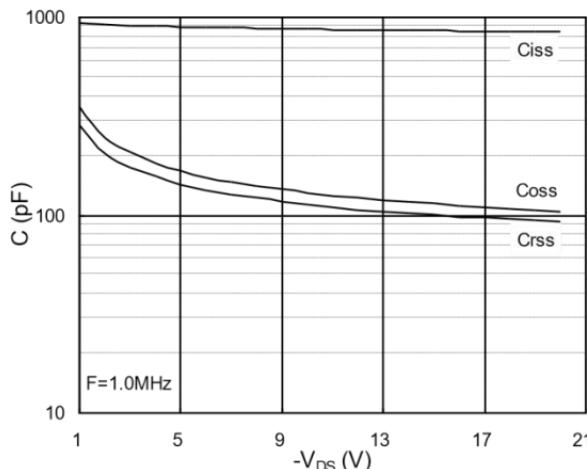


Fig.7 Capacitance

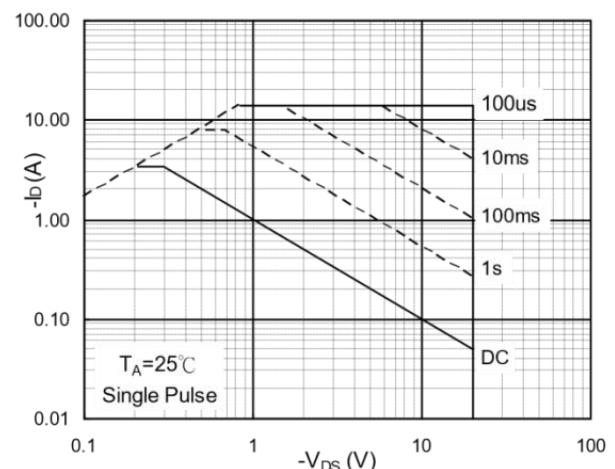


Fig.8 Safe Operating Area

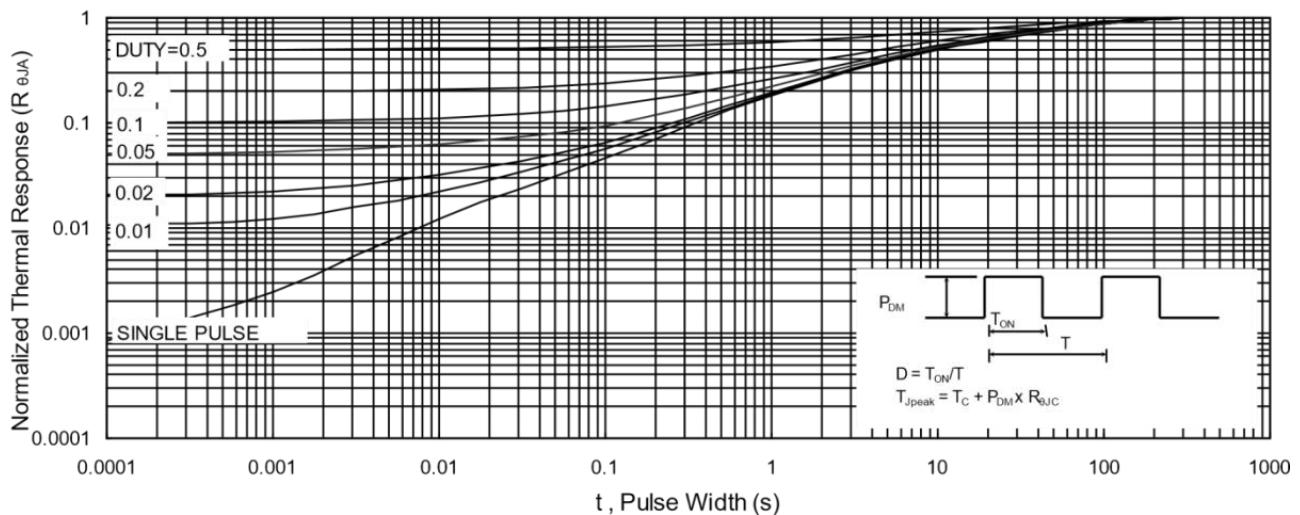


Fig.9 Normalized Maximum Transient Thermal Impedance

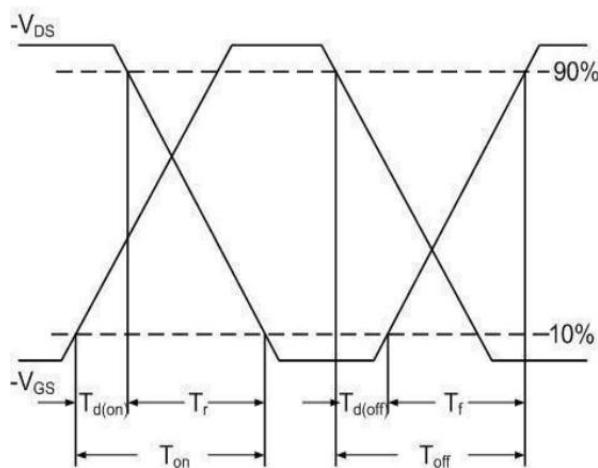


Fig.10 Switching Time Waveform

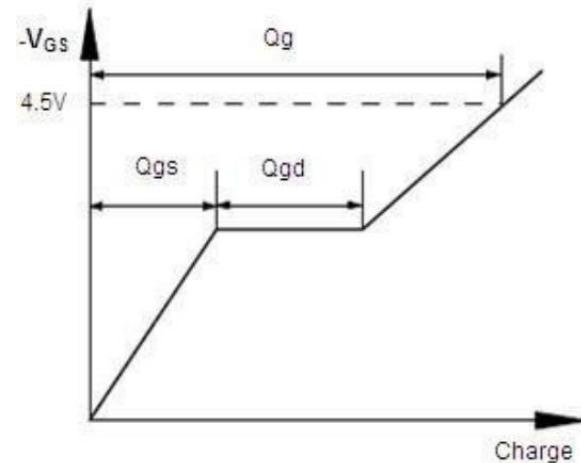
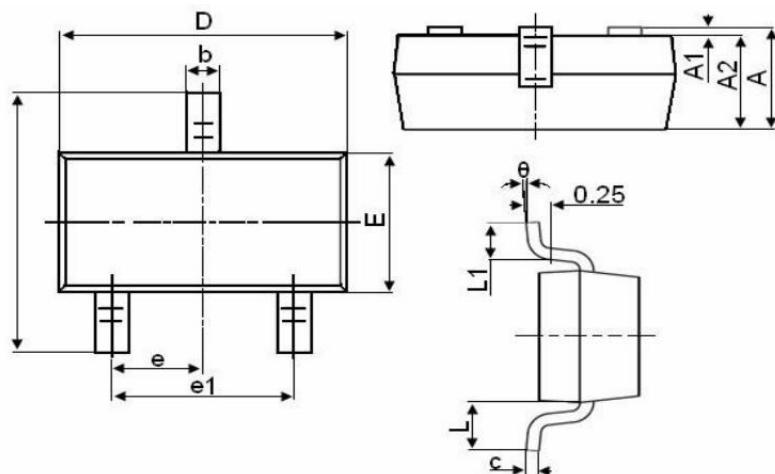


Fig.11 Gate Charge Waveform

## Package Mechanical Data-SOT23-XC-Single



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23		3000